

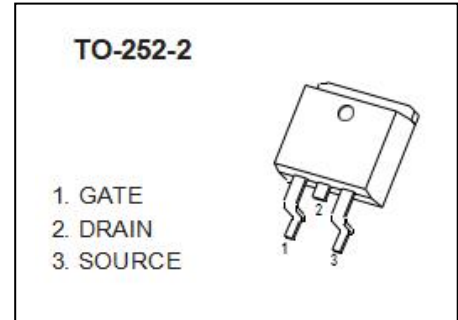


CHONGQING CLOUDCHILD TECHNOLOGY CO.,LTD

TO-252-2L Plastic-Encapsulate MOSFETS

CCMC50N06S N-Channel Power MOSFET

V_{DS}	$R_{DS(ON)}$ (Typ.)	I_D
60 V	7.5m Ω @10V 10m Ω @4.5V	50A



DESCRIPTION

The CCMC50N06S provides excellent $R_{DS(ON)}$ with low gate charge.

It can be used in a wide variety of applications.

FEATURES

- High density cell design for ultra low $R_{DS(ON)}$
- Repetitive avalanche rated
- AEC Q101 Qualified

APPLICATIONS

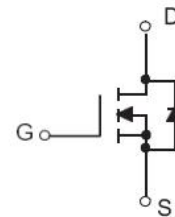
- 12V/24V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- High-frequency switching and synchronous rectification

MARKING



CCMC50N06S =Part No.
XXXXXXXX = Code.

EQUIVALENT CIRCUIT



ABSOLUTE MAXIMUM RATINGS($T_c=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain-Source Voltage	V_{DS}	60	V	
Gate-Source Voltage	V_{GS}	± 20	V	
Continuous Drain Current ¹	I_D	50	A	
Pulsed Drain Current ²	I_{DM}	200	A	
Single Pulse Avalanche Energy ²³	E_{AS}	110	mJ	
Total Power Dissipation	P_D	52	W	
Thermal Resistance from Junction to Case ²	$R_{\theta JC}$	2.9	$^{\circ}\text{C}/\text{W}$	
SMD version, device on PCB ⁴	$R_{\theta JA}$	minimal footprint		62
		6cm ² cooling area		40
Junction Temperature	T_J	175	$^{\circ}\text{C}$	
Storage Temperature	T_{STG}	-55~ +175	$^{\circ}\text{C}$	
Soldering Temperature , for 10S(1.6mm from case)	-	260	$^{\circ}\text{C}$	

Notes:

1. Current is limited by package; with a $R_{thjc} = 2.9^{\circ}\text{C}/\text{W}$ the chip is able to carry 67A at 25°C .
2. Specified by design. Not subject to production test.
3. EAS condition: $T_j=25^{\circ}\text{C}$, $V_{DD}=30\text{V}$, $L=0.5\text{mH}$, $R_G=25\Omega$, $I_D=21\text{A}$, Starting $T_J = 25^{\circ}\text{C}$.
4. Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

MOSFET ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 60V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
On characteristics						
Gate-threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.5	1.7	2.5	V
Static drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 50A$		7.5	10	m Ω
		$V_{GS} = 4.5V, I_D = 25A$		10	14	m Ω
Forward transconductance	g_{fs}	$V_{DS} = 10V, I_D = 10A$		65		S
Dynamic characteristics¹						
Input capacitance	C_{iss}	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1MHz$		1560	2028	pF
Output capacitance	C_{oss}			351	456	
Reverse transfer capacitance	C_{rss}			25	33	
Gate resistance	R_g	$f = 1MHz$		1.7		Ω
Switching characteristics¹						
Total gate charge	Q_g	$V_{GS} = 0-10V, V_{DD} = 48V,$ $I_D = 50A$		30	40	nC
Gate-source charge	Q_{gs}			10	12	
Gate-drain charge	Q_{gd}			3	7	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 30V, I_D = 50A,$ $V_{GS} = 10V, R_G = 3.5\Omega$		6		ns
Turn-on rise time	t_r			2		
Turn-off delay time	$t_{d(off)}$			26		
Turn-off fall time	t_f			5.5		
Drain-Source Diode Characteristics						
Drain-source diode forward voltage	V_{SD}	$V_{GS} = 0V, I_S = 50A$		0.87	1.3	V
Continuous drain-source diode forward Current ¹²	I_S	-			50	A
Pulsed drain-source diode forward current ¹	I_{SM}	-			200	A
Reverse recovery time ¹	T_{rr}	$I_F = 50A,$ $dI/dt = 100A/\mu s, V_R = 30V$		22		ns
Reverse recovery charge ¹	Q_{rr}			20		nC

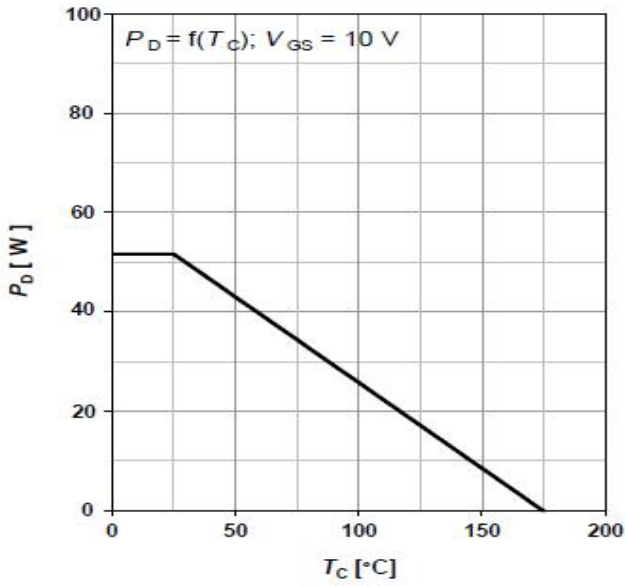
Note :

1. Specified by design. Not subject to production test.

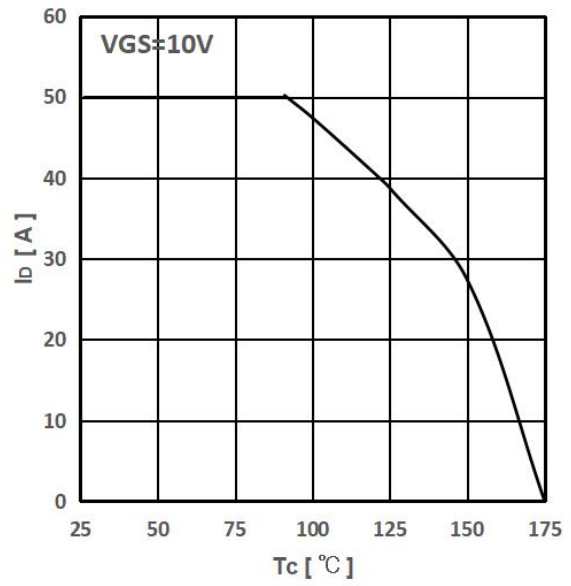
2. Current is limited by package; with a $R_{thjc} = 2.9 \text{ }^\circ\text{C/W}$ the chip is able to carry 67A at 25°C.

Typical Characteristics

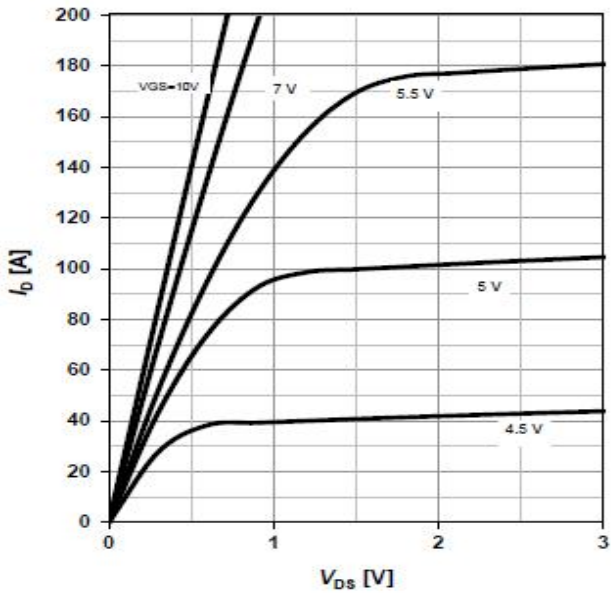
PD -- Tc



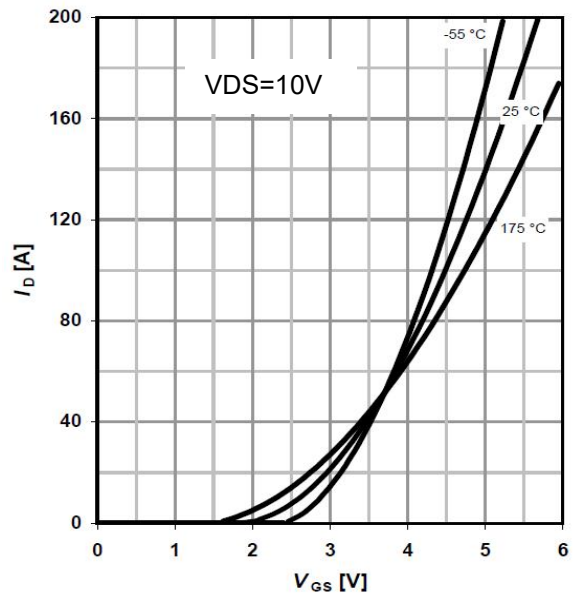
ID -- Tc



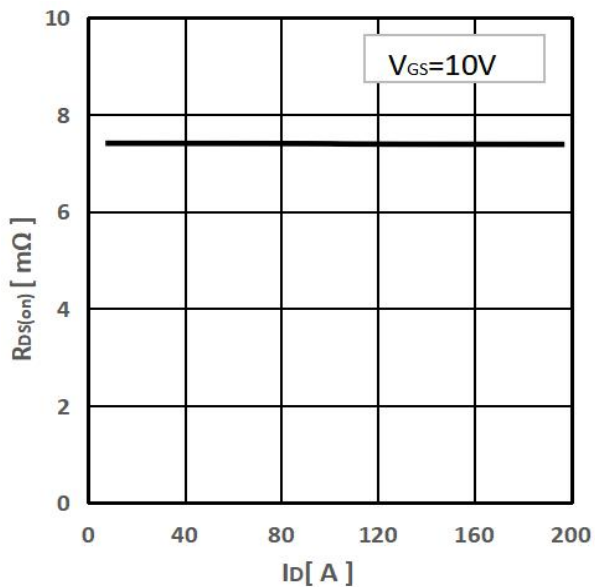
ID -- VDS



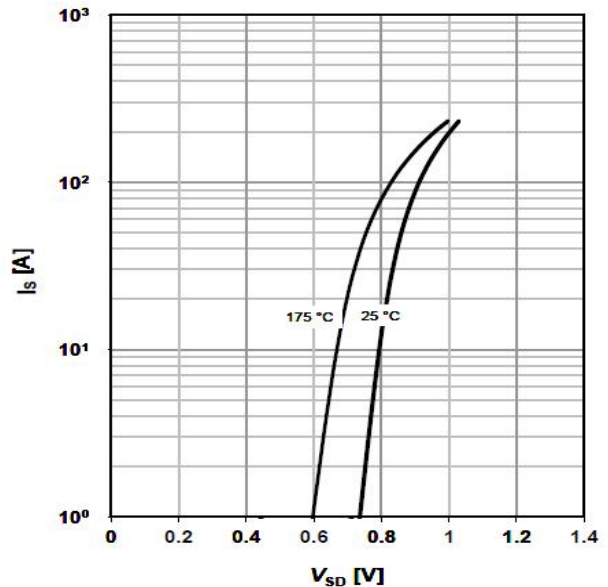
ID -- VGS



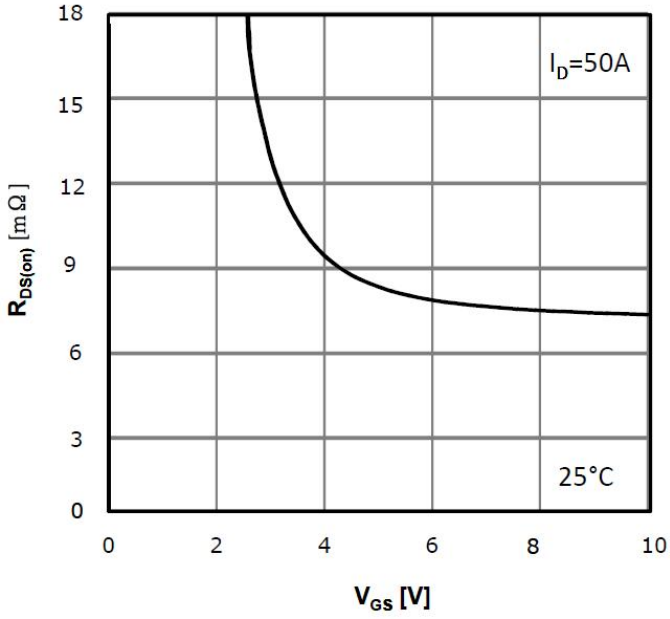
RDS(on) -- ID



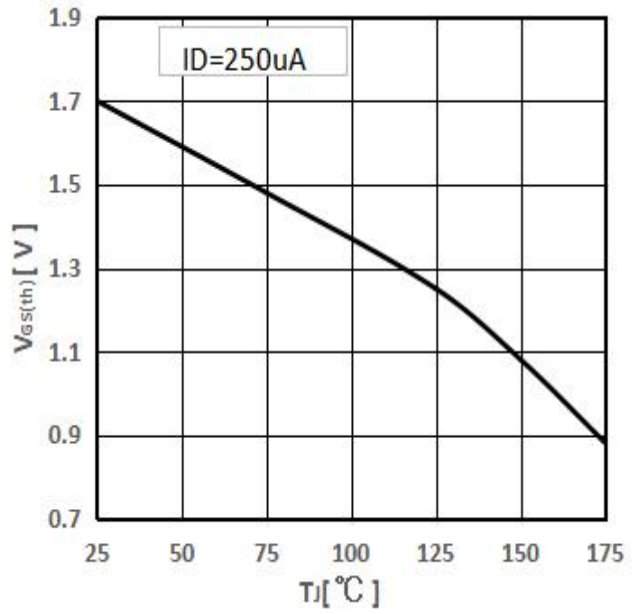
IS -- VSD



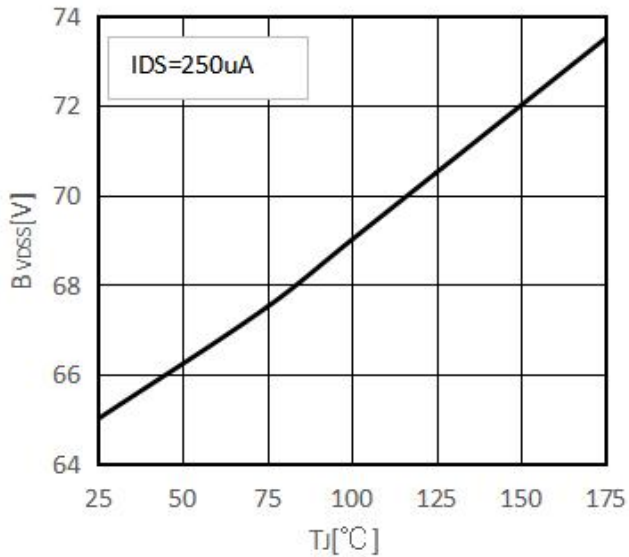
RDS(on) -- VGS



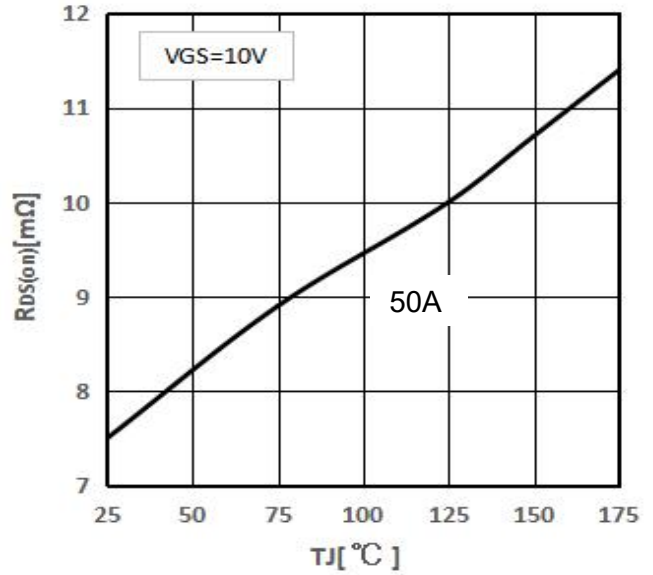
Threshold Voltage



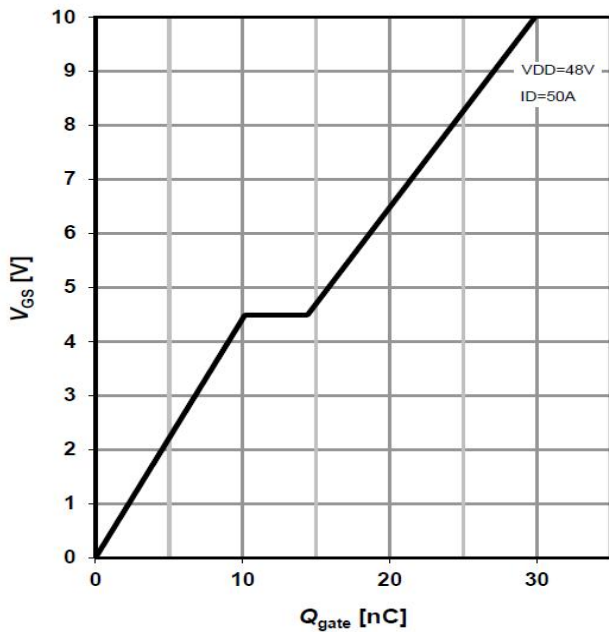
Drain-source breakdown voltage



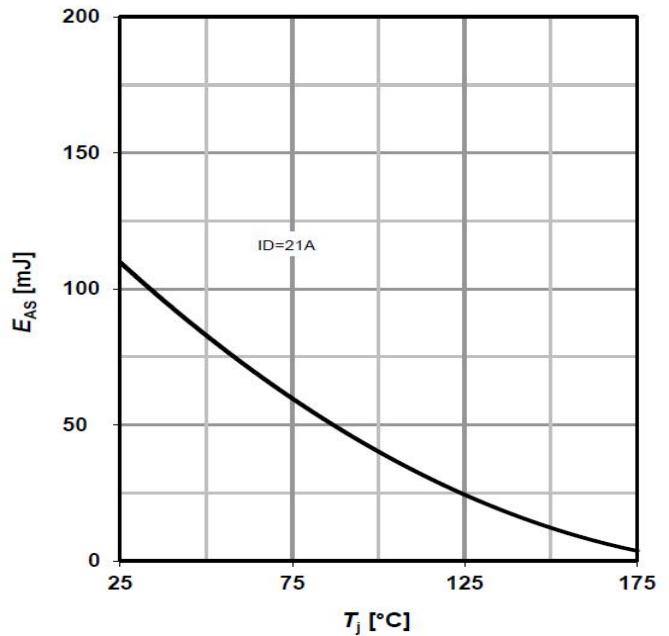
RDS (on) -- Tj



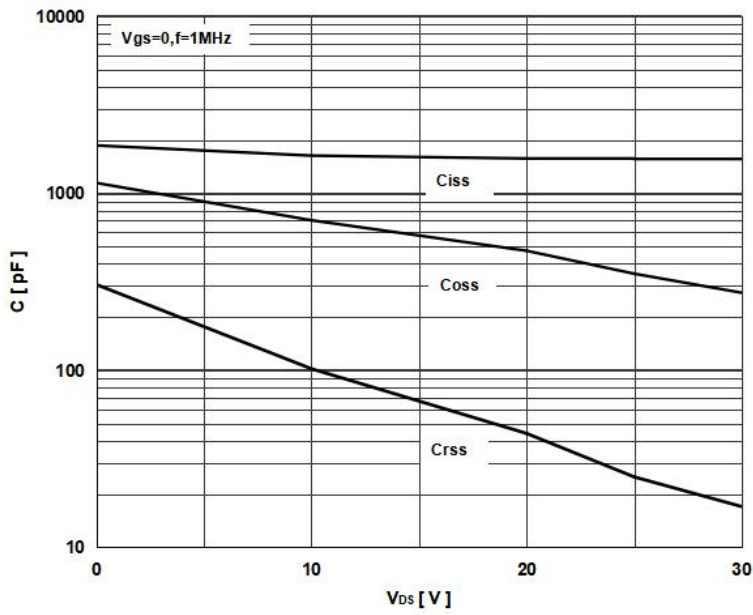
Typ.gate charge



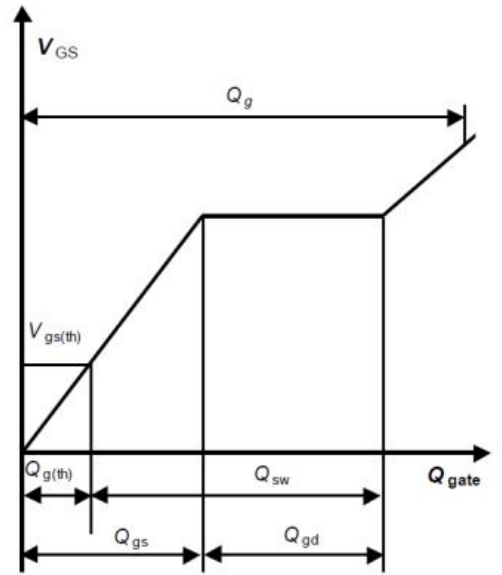
Avalanche energy



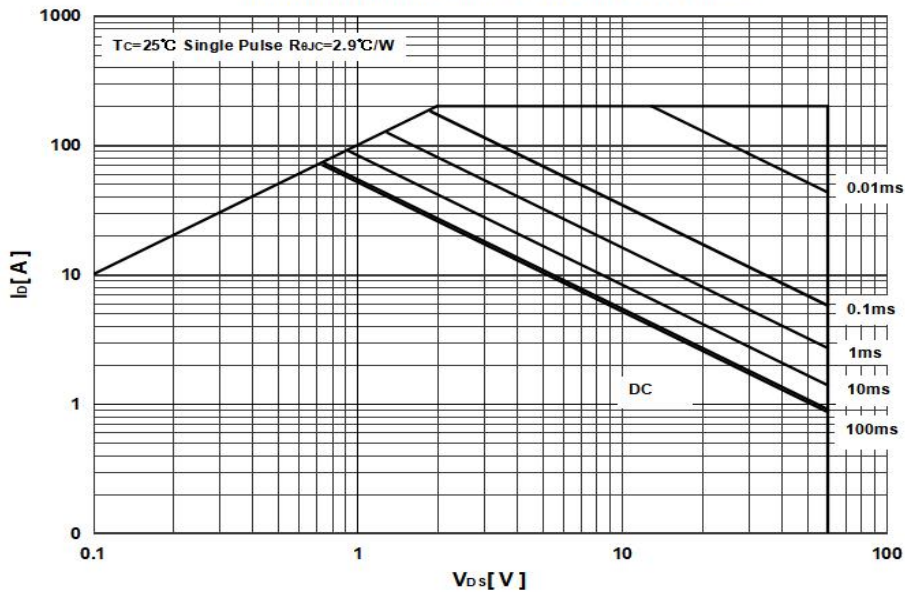
Typ. capacitance



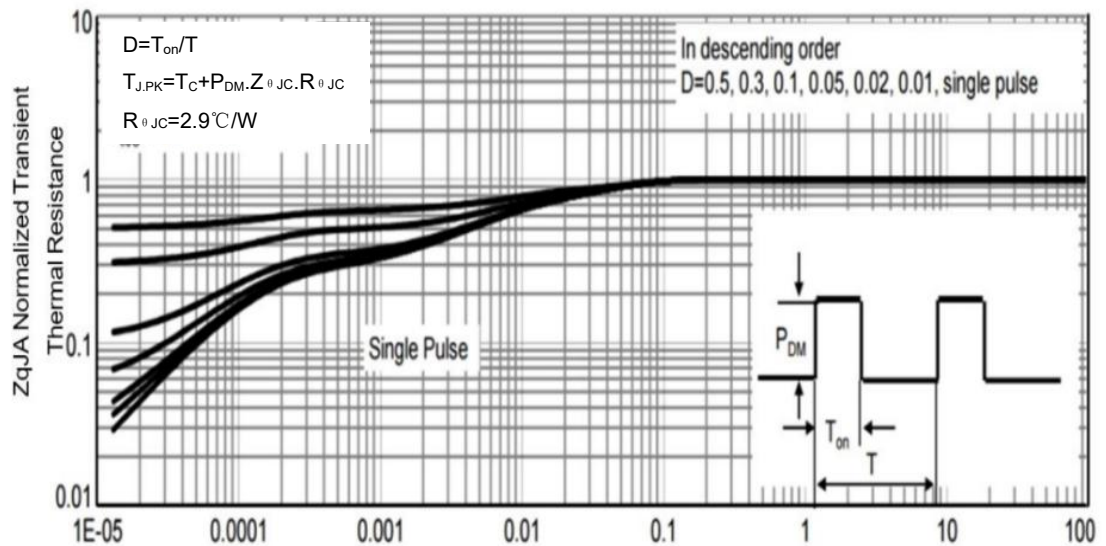
Gate charge waveforms



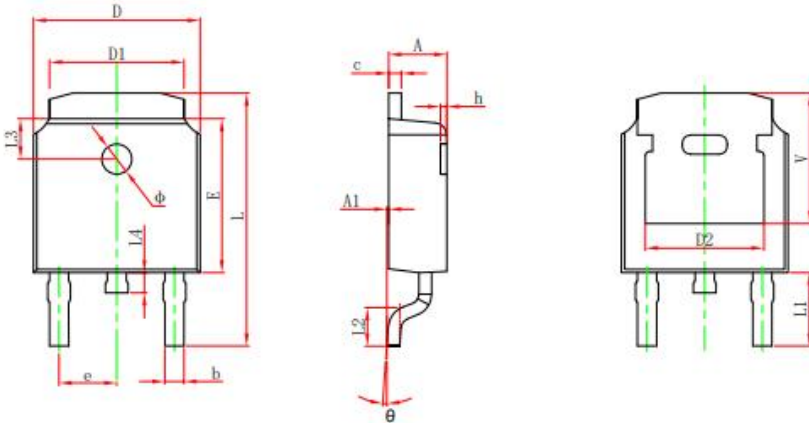
Maximum Forward Biased Safe Operating Area



Normalized Thermal Transient Impedance

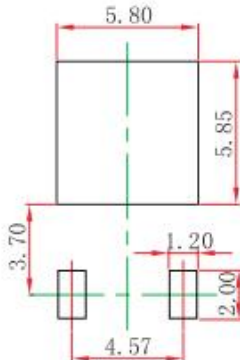


TO-252-2L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	

TO-252-2L Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: 0.5mm.
3. The pad layout is for reference purposes only.

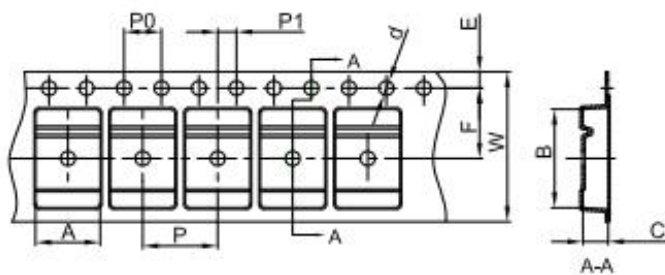
NOTICE

Cloudchild reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. Cloudchild does not assume any liability arising out of the application or use of any product described herein.

ChongQing Cloudchild Technology Co., Ltd. (short for Cloudchild) exerts the greatest possible effort to ensure high quality and reliability. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing Cloudchild products, to comply with the standards of safety in making a safe design for the entire system, including redundancy, fire-prevention measures, and malfunction prevention, to prevent any accidents, fires, or community damage that may ensue. In developing your designs, please ensure that Cloudchild products are used within specified operating ranges as set forth in the most recent Cloudchild products specifications.

TO-252-2L Tape and Reel

TO-252 Embossed Carrier Tape

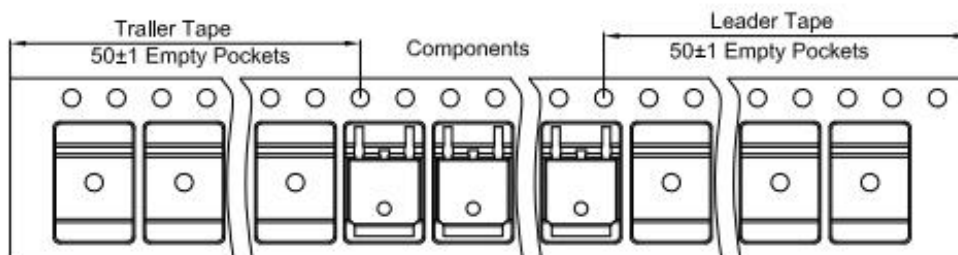


Packaging Description:

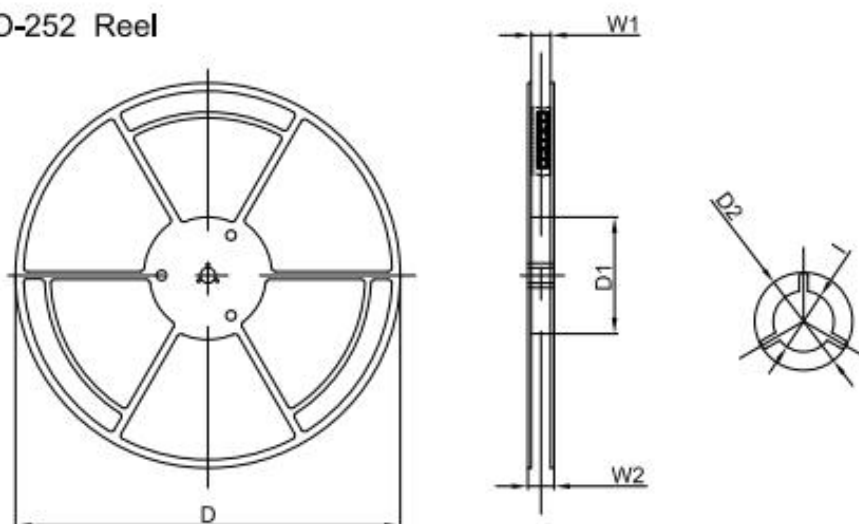
TO-252 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 25,00 units per 13" or 33.0 cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
TO-252	6.90	10.50	2.70	Ø1.55	1.75	7.50	4.00	8.00	2.00	16.00

TO-252 Tape Leader and Trailer



TO-252 Reel



Dimensions are in millimeter						
Reel Option	D	D1	D2	W1	W2	L
13"Dia	330.00	100.00	Ø21.00	16.40	21.00	Ø13.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
2,500 pcs	13Inch	2,500 pcs	340×336×29	25,000 pcs	353×346×365	

Date of change	Rev #	revise content
2023/11/16	A/0	/